

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSII<sup>5</sup>)

# 2SK1359

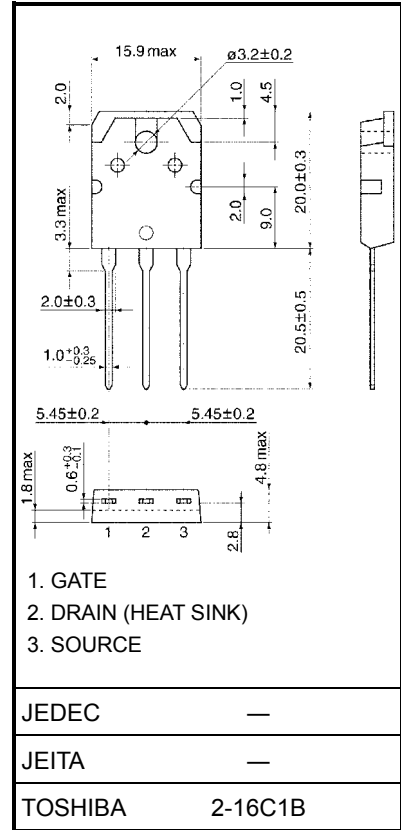
DC-DC Converter and Motor Drive Applications

Unit: mm

- Low drain-source ON resistance :  $R_{DS(ON)} = 3.0 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 2.0 S$  (typ.)
- Low leakage current :  $I_{DSS} = 300 \mu A$  (max) ( $V_{DS} = 800 V$ )
- Enhancement-mode :  $V_{th} = 1.5 \sim 3.5 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	1000	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )		$V_{DGR}$	1000	V
Gate-source voltage		$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	5	A
	Pulse (Note 1)	$I_{DP}$	15	
Drain power dissipation ( $T_c = 25^\circ C$ )		$P_D$	125	W
Channel temperature		$T_{ch}$	150	°C
Storage temperature range		$T_{stg}$	-55~150	°C



Weight: 4.6 g (typ.)

## Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.0	°C / W
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	50	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device.  
Please handle with caution.

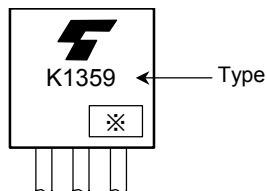
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 50$	nA
Drain cut-off current		$I_{DSS}$	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	—	—	300	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	1000	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.5	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 2\text{ A}$	—	3.0	3.8	$\Omega$
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 20\text{ V}, I_D = 2\text{ A}$	1.0	2.0	—	S
Input capacitance		$C_{iss}$	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	700	—	pF
Reverse transfer capacitance		$C_{rss}$		—	55	—	
Output capacitance		$C_{oss}$		—	100	—	
Switching time	Rise time	$t_r$	<p><math>I_D = 2\text{ A}</math> <math>V_{GS} = 10\text{ V}</math> <math>V_{DS} = 0\text{ V}</math> <math>R_L = 200\ \Omega</math> <math>V_{DD} \approx 400\text{ V}</math> Duty <math>\leq 1\%</math>, <math>t_w = 10\ \mu\text{s}</math></p>	—	18	—	ns
	Turn-on time	$t_{on}$		—	30	—	
	Fall time	$t_f$		—	12	—	
	Turn-off time	$t_{off}$		—	70	—	
Total gate charge (Gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx 400\text{ V}, V_{GS} = 10\text{ V}, I_D = 4\text{ A}$	—	60	—	nC
Gate-source charge		$Q_{gs}$		—	35	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	25	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

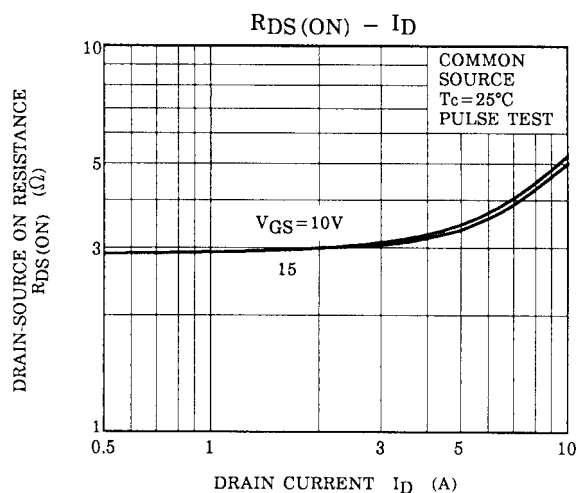
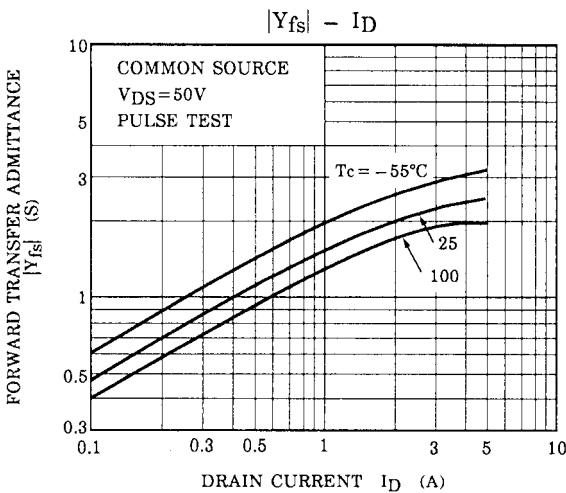
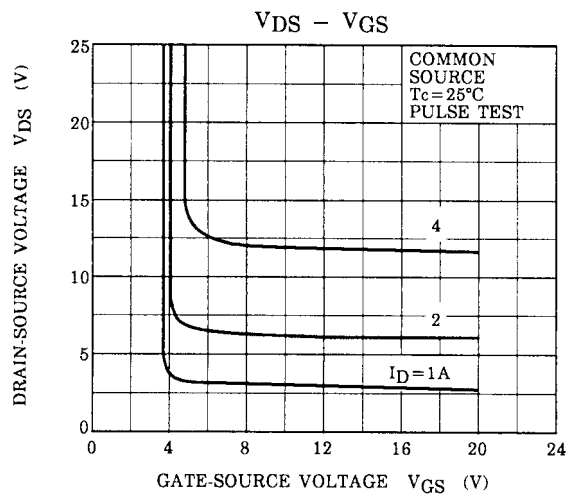
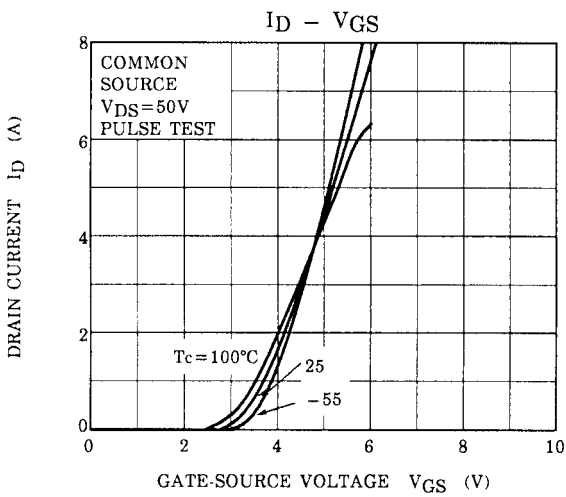
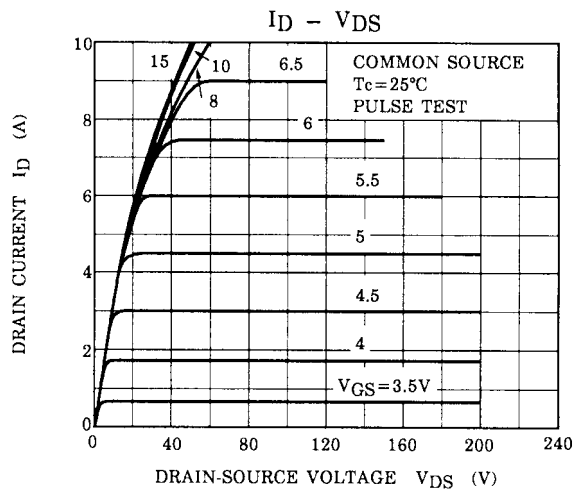
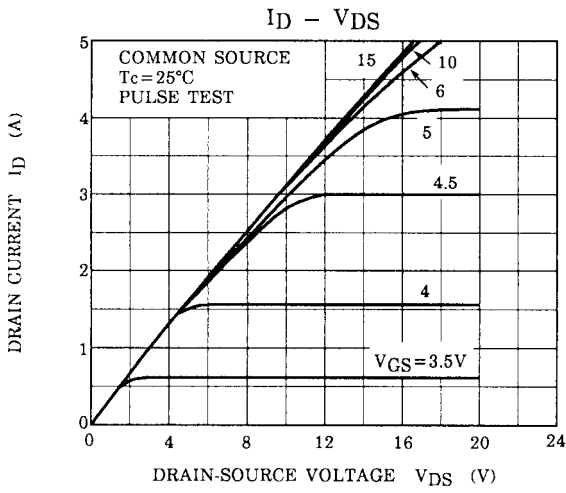
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	5	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	15	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 4\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.9	V

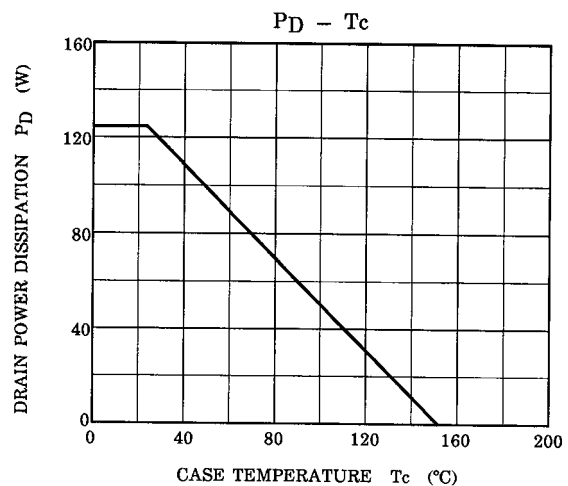
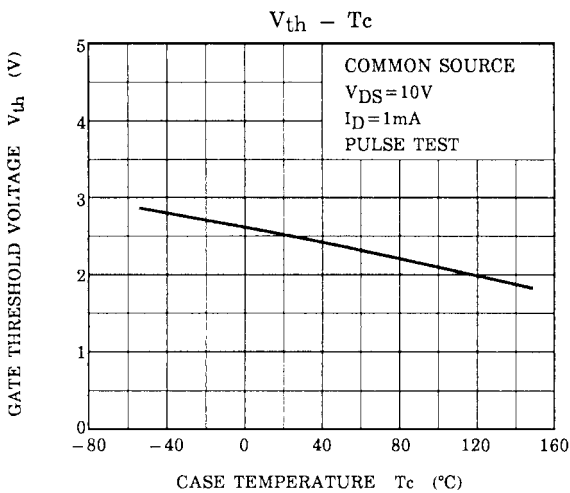
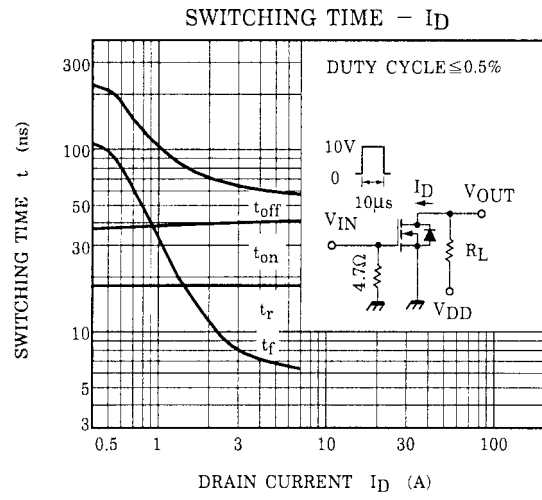
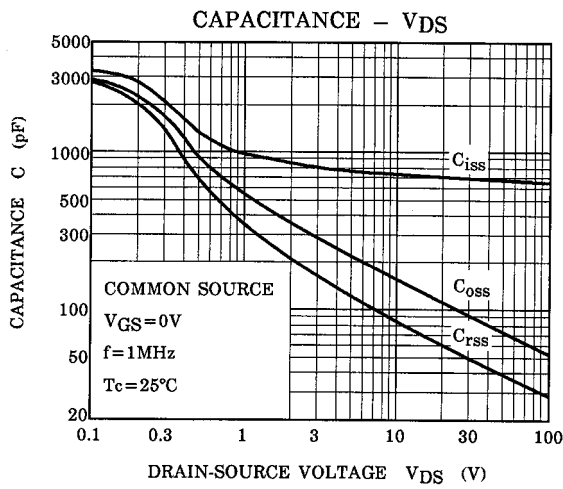
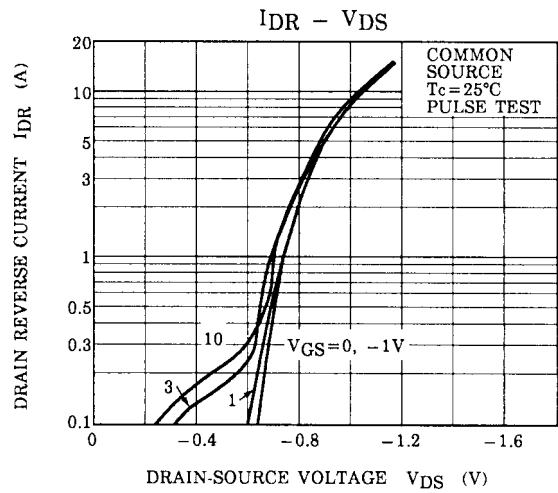
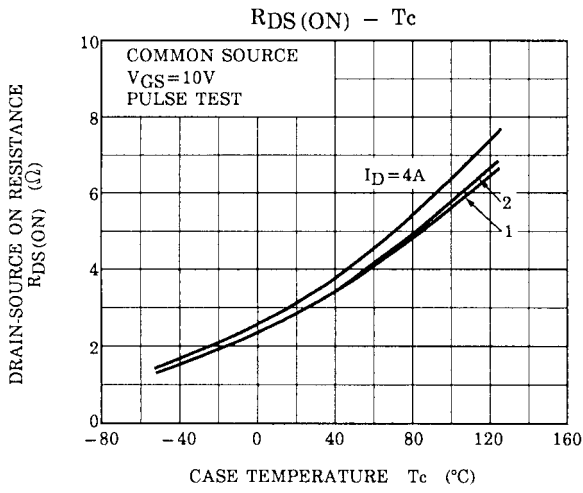
## Marking

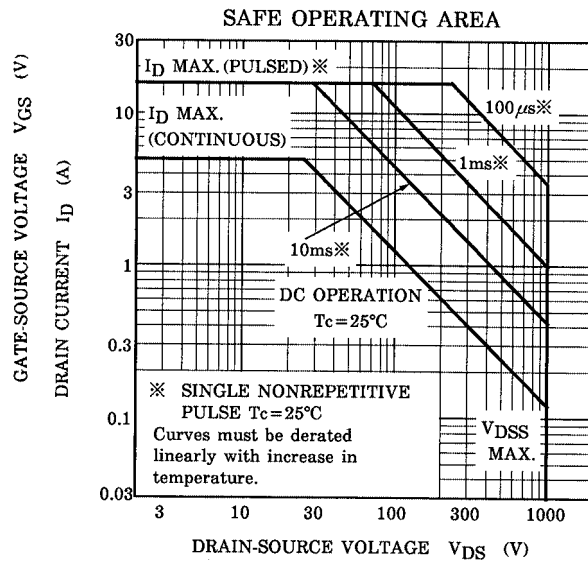
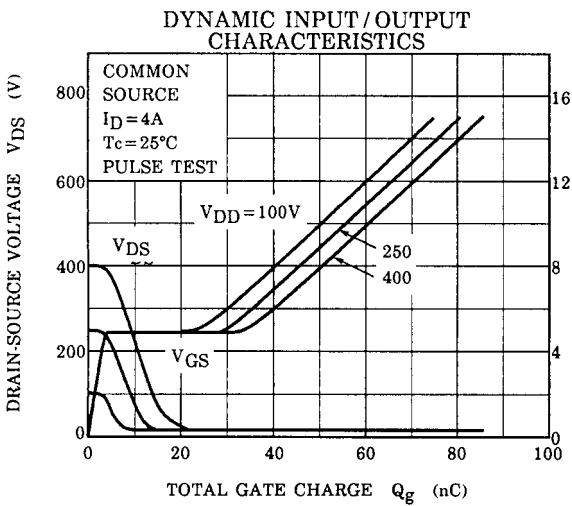
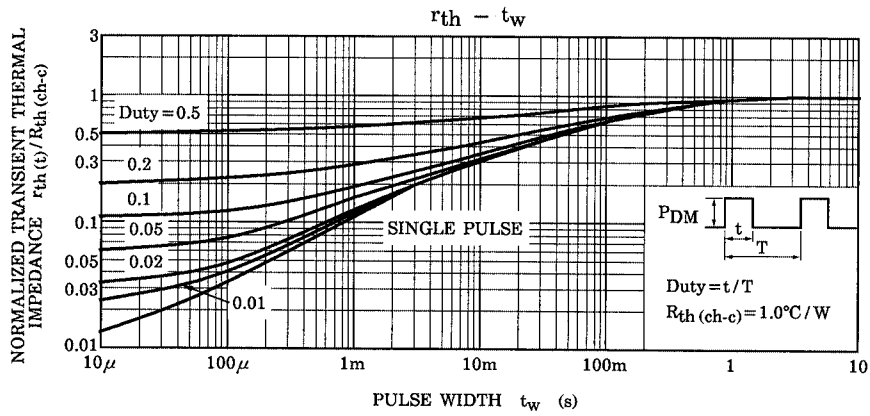


※ Lot Number

Month (starting from alphabet A)  
 Year (last number of the christian era)







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